

# FQA8N100C

## 1000V N-Channel MOSFET

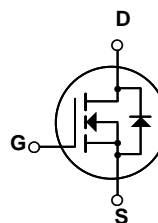
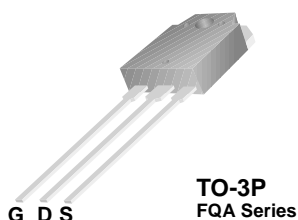
### Features

- 8A, 1000V,  $R_{DS(on)} = 1.45\Omega @ V_{GS} = 10V$
- Low gate charge (typical 53 nC)
- Low  $C_{rss}$  (typical 16 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

### Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficient switched mode power supplies.



### Absolute Maximum Ratings

Symbol	Parameter	FQA8N100C	Unit
$V_{DSS}$	Drain-Source Voltage	1000	V
$I_D$	Drain Current - Continuous ( $T_C = 25^\circ\text{C}$ ) - Continuous ( $T_C = 100^\circ\text{C}$ )	8 5	A A
$I_{DM}$	Drain Current - Pulsed (Note 1)	32	A
$V_{GSS}$	Gate-Source voltage	$\pm 30$	V
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	850	mJ
$I_{AR}$	Avalanche Current (Note 1)	8	A
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	22.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.0	V/ns
$P_D$	Power Dissipation ( $T_C = 25^\circ\text{C}$ ) - Derate above $25^\circ\text{C}$	225 1.79	W W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	Min.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	0.56	$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink	0.24	--	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	$^\circ\text{C}/\text{W}$

## Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FQA8N100C	FQA8N100C	TO-3P	--	--	30

## Electrical Characteristics T<sub>C</sub> = 25°C unless otherwise noted

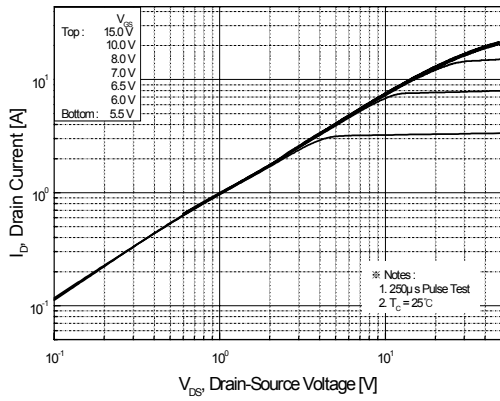
Symbol	Parameter	Conditions	Min.	Typ.	Max	Units
<b>Off Characteristics</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	1000	--	--	V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250μA, Referenced to 25°C	--	1.4	--	V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 1000V, V <sub>GS</sub> = 0V V <sub>DS</sub> = 800V, T <sub>C</sub> = 125°C	--	--	10 100	μA μA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30V, V <sub>DS</sub> = 0V	--	--	100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30V, V <sub>DS</sub> = 0V	--	--	-100	nA
<b>On Characteristics</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	3.0	--	5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 4A	--	1.2	1.45	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 50V, I <sub>D</sub> = 4A (Note 4)	--	8.0	--	S
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz	--	2475	3220	pF
C <sub>oss</sub>	Output Capacitance		--	195	255	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		--	16	24	pF
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 500V, I <sub>D</sub> = 8A R <sub>G</sub> = 25Ω  (Note 4, 5)	--	50	110	ns
t <sub>r</sub>	Turn-On Rise Time		--	95	200	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		--	122	254	ns
t <sub>f</sub>	Turn-Off Fall Time		--	80	170	ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = 800V, I <sub>D</sub> = 8A V <sub>GS</sub> = 10V  (Note 4, 5)	--	53	70	nC
Q <sub>gs</sub>	Gate-Source Charge		--	13	--	nC
Q <sub>gd</sub>	Gate-Drain Charge		--	23	--	nC
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current		--	--	8	A
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current		--	--	32	A
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0V, I <sub>S</sub> = 8A	--	--	1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0V, I <sub>S</sub> = 8A di <sub>F</sub> /dt = 100A/μs  (Note 4)	--	620	--	ns
Q <sub>rr</sub>	Reverse Recovery Charge		--	5.2	--	μC

### NOTES:

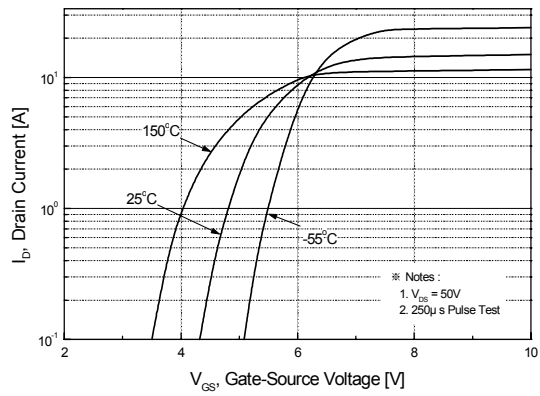
1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L = 25mH, I<sub>AS</sub> = 8A, V<sub>DD</sub> = 50V, R<sub>G</sub> = 25Ω, Starting T<sub>J</sub> = 25°C
3. I<sub>SD</sub> ≤ 8A, di/dt ≤ 200A/μs, V<sub>DD</sub> ≤ BV<sub>DSS</sub>, Starting T<sub>J</sub> = 25°C
4. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%
5. Essentially Independent of Operating Temperature Typical Characteristics

## Typical Performance Characteristics

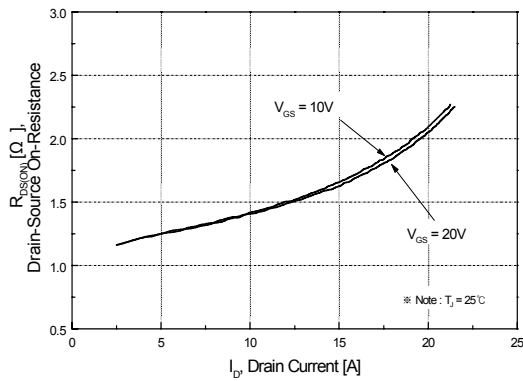
**Figure 1. On-Region Characteristics**



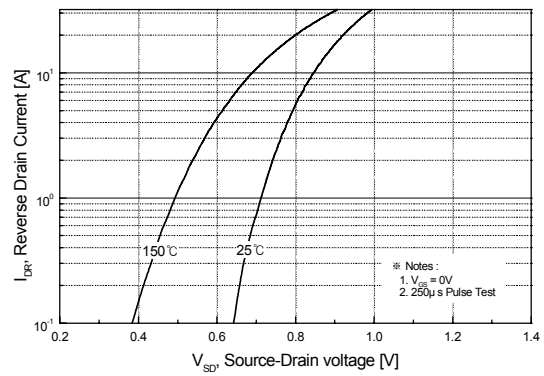
**Figure 2. Transfer Characteristics**



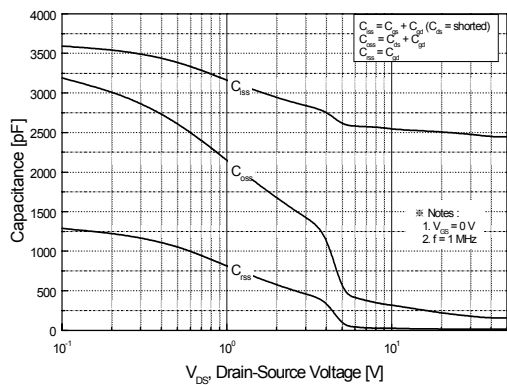
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



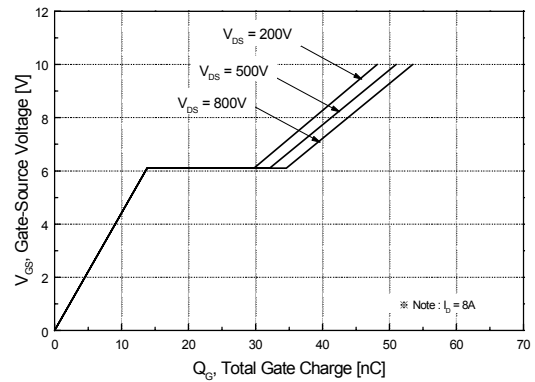
**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**



**Figure 5. Capacitance Characteristics**

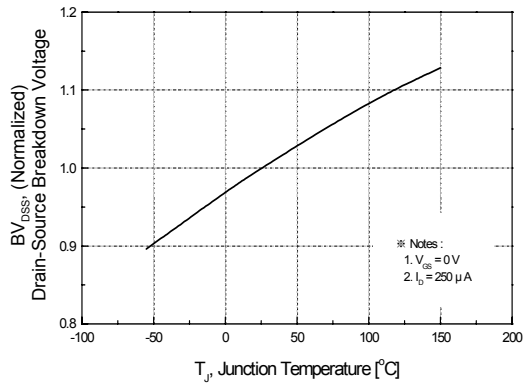


**Figure 6. Gate Charge Characteristics**

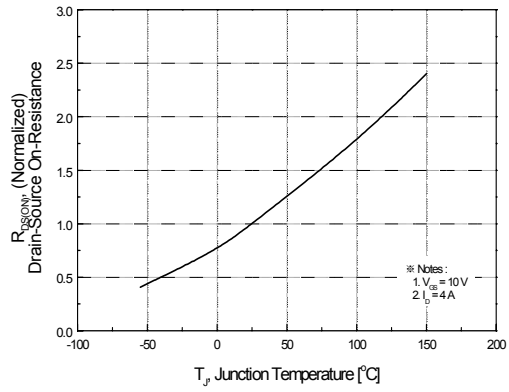


**Typical Performance Characteristics** (Continued)

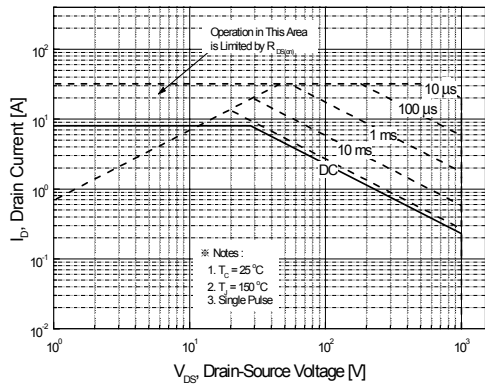
**Figure 7. Breakdown Voltage Variation vs. Temperature**



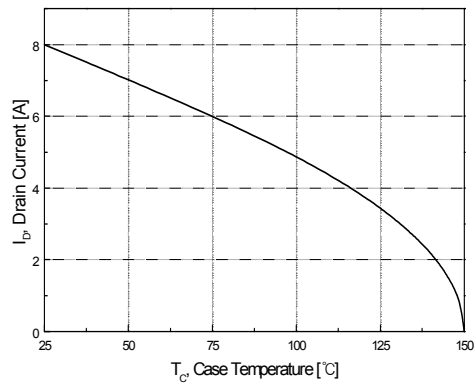
**Figure 8. On-Resistance Variation vs. Temperature**



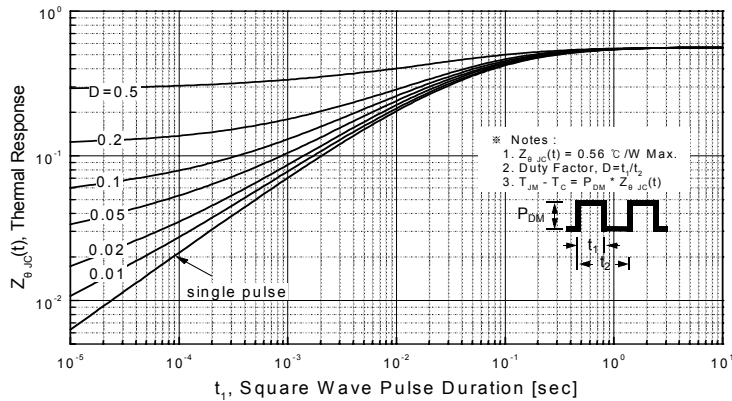
**Figure 9. Maximum Safe Operating Area**



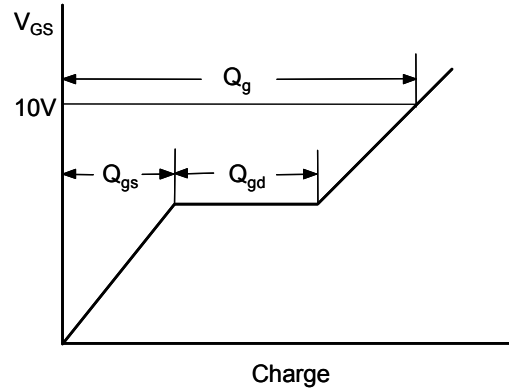
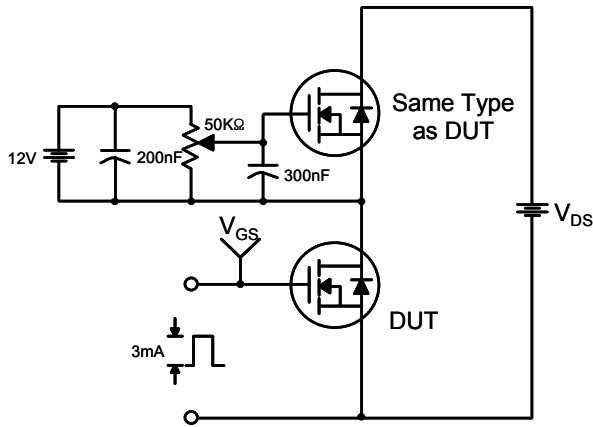
**Figure 10. Maximum Drain Current vs. Case Temperature**



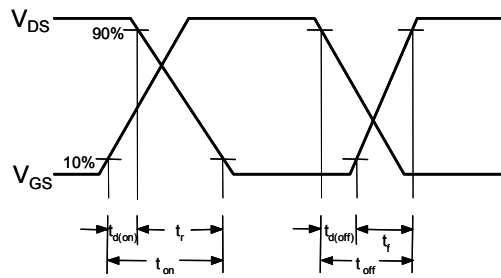
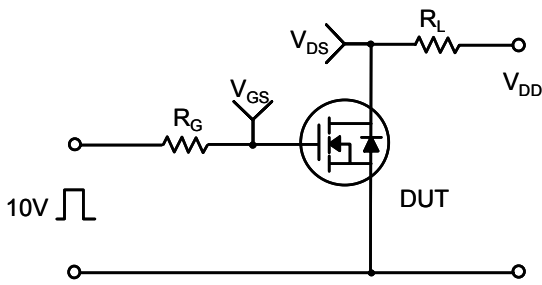
**Figure 11. Transient Thermal Response Curve**



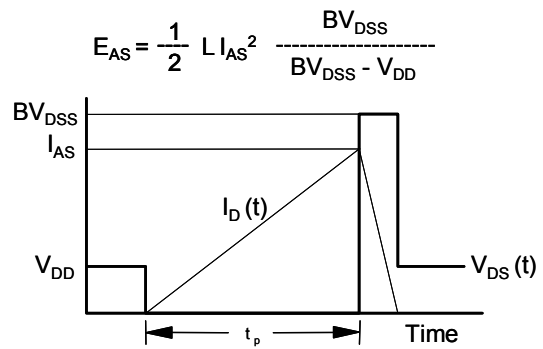
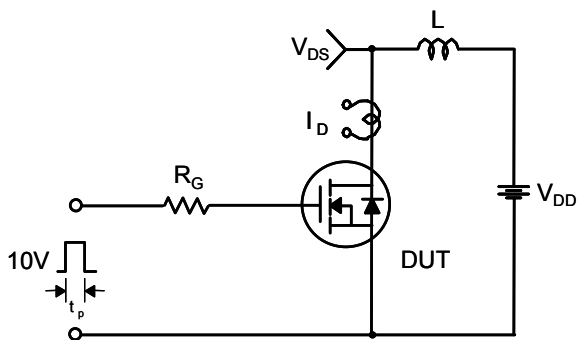
**Gate Charge Test Circuit & Waveform**



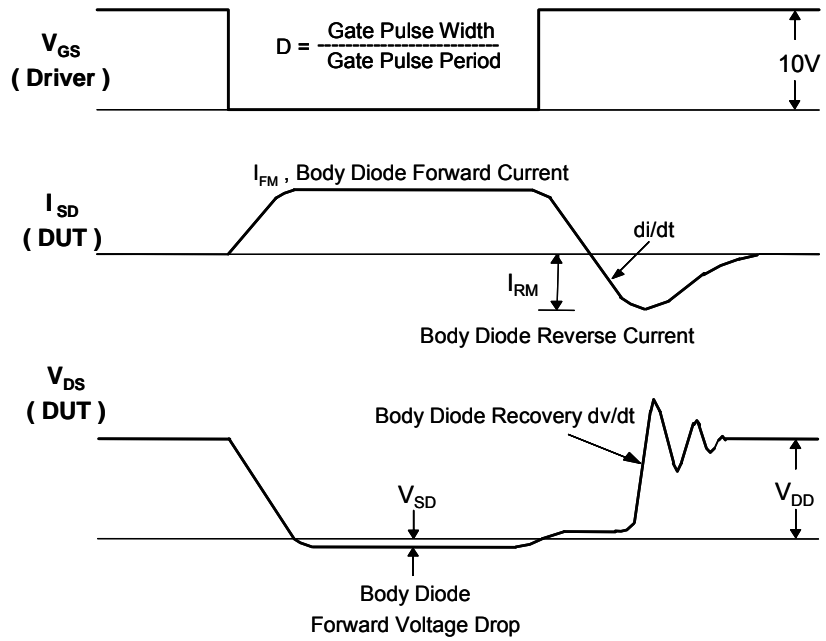
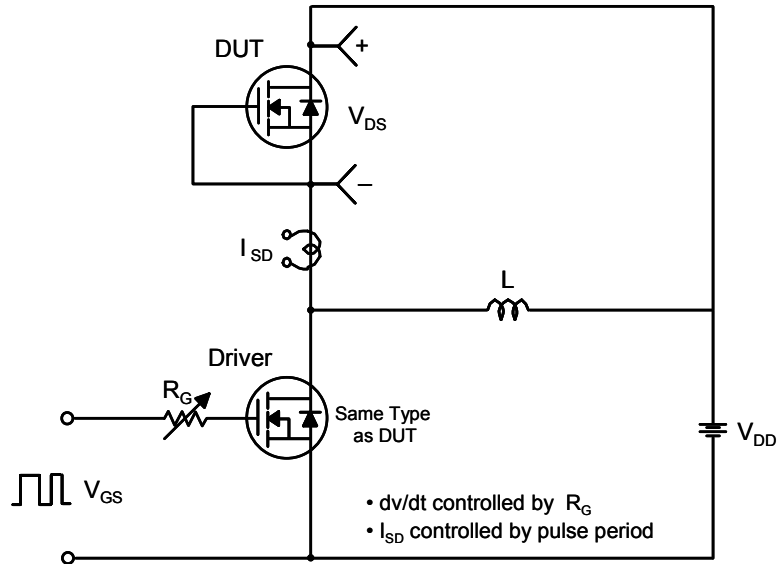
**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching Test Circuit & Waveforms**

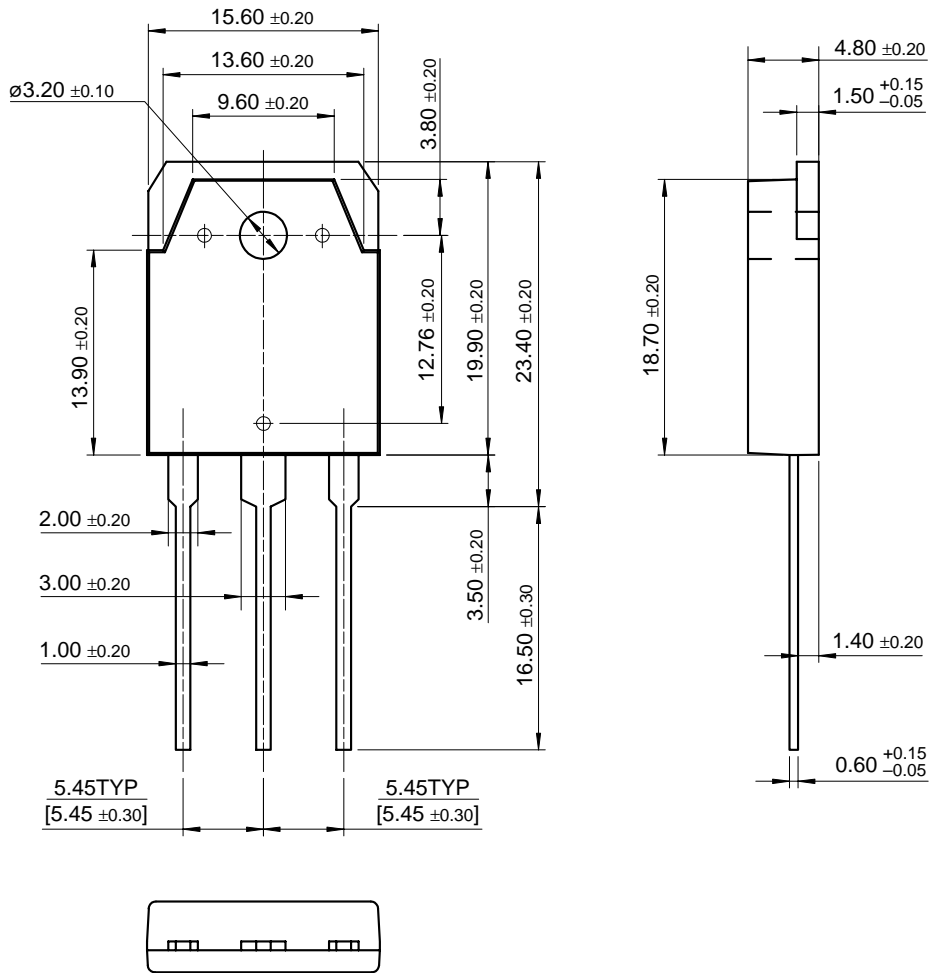


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Mechanical Dimensions

TO-3P



Dimensions in Millimeters

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